

Investor Presentation

July 2022

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Company Overview

Leading Provider of Specialty Memory Technology and Products to Mission-Critical Applications from the **Data Center** to **Industrial and IoT End Point** applications

Headquarters Chandler, AZ

Established 2008

Listed NASDAQ: MRAM

Segment Semiconductor Memory

Total 2021 Revenue \$55.1M

Diversified Customer Base

2,000+

Across multiple markets

In Production over 12 years

120M+

MRAM Units shipped

Strong IP Portfolio

650+

Patents and applications WW

Focused on differentiated value and long-term growth in stable and growing markets



MRAM Capabilities



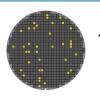
Design Services

- Discrete Memory Device or Embedded
- Custom STT-MRAM
- Full chip enablement or support in-house design team
- Ability to leverage proven Everspin commercial IP
- Experience with multiple successful engagements



8" BEOL Manufacturing

- Everspin owned and operated 8" line in USA
- Any foundry CMOS
- In production operation for over 15 years
- Trusted by US Gov programs and commercial
- Everspin Commercial Toggle MRAM line
- R&D capabilities



12" 40/28/22nm STT MRAM

- Partnership with GLOBALFOUNDRIES
- Manufactured fully at GF
- Commercially proven STT MRAM Line
- 22nm FD SOI products in design
 - available for rad hard designs

Everspin offers the widest capability to develop fully customized STT-MRAM – Design to Manufacturing



The Executive Team



President & CEO



Anuj Aggarwal

Chief Financial Officer



Thermo Fisher SCIENTIFIC

David Schrenk

VP, Sales & Business Development



Amit Shah

VP, Backend Operations





Yong Kim

VP, Product Development



Kerry Nagel

VP, Technology R&D



Khaldoun Barakat

VP, FAB Operations & Quality

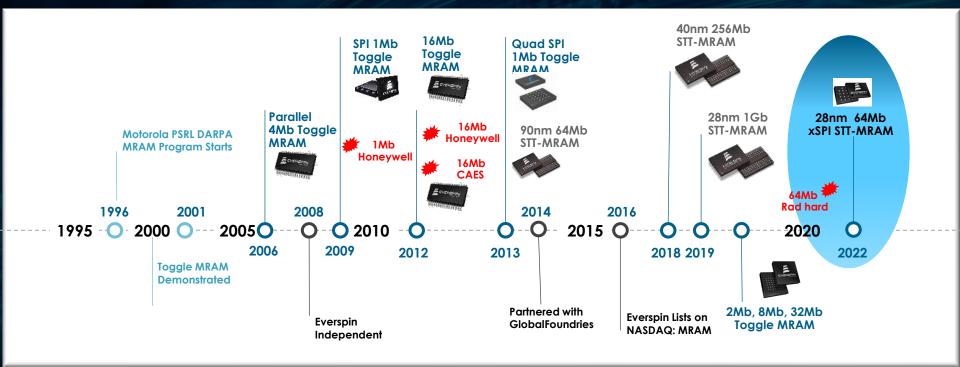




Proven Team With Strong Experience In Delivering Market Leading Technology



MRAM Leadership Through a Heritage of Innovation



uslom Rad-Hard – Everspin MRAM Technology



Only MRAM Demonstrates The Promise of Universal Memory

PERSISTENCE

Maintains memory contents without requiring power

PERFORMANCE

SRAM & DRAM-like performance with low latency

ENDURANCE

Superior durability supports memory workloads without sophisticated management

RELIABILITY

Best-in-class robustness designed and tested for extreme conditions





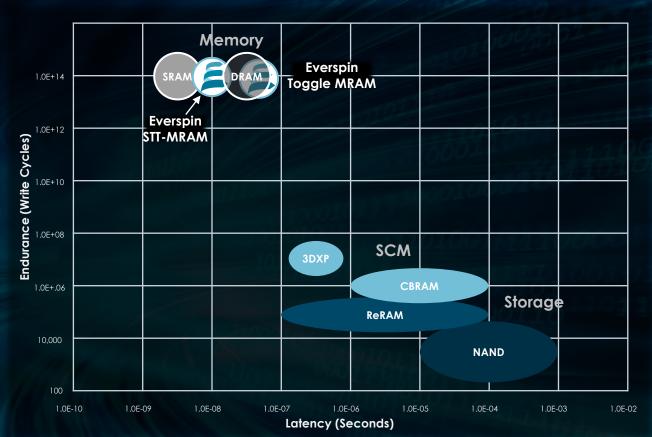




MRAM as a CPU-attached memory (like SRAM/DRAM) that brings non-volatile capability (like Flash)



MRAM Brings Native Persistence to Memory Workloads



MRAM COMBINES PERFORMANCE OF MEMORY WITH PERSISTENCE OF STORAGE

- Persistence: Months to decades of data retention without power or refresh
- Performance: Read/write similar to DRAM
- Endurance: Handles memory workloads



5G Opens A Universe of MRAM Applications

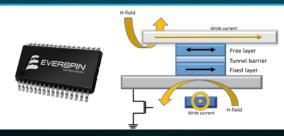
Core Edge **End Points** 27B Networked Industrial & By 2025 75% of enterprise data 175 Zettabytes of will be created and processed loT Devices by 2021 data by 2025 outside the Datacenter **Producing 79 ZB** Industrial Gaming Enterprise **Automation** Storage Smart Medical (W)) Meter (W)) Electric (W) 5G Transportation Charaina **Fabric** Persistent Enterprise Accelerator Memory Infrastructure Server RAID

5G brings unprecedented bandwidth - expected to increase Industrial and IoT End Point persistent memory needs and drive lower Core latency in the Data Center



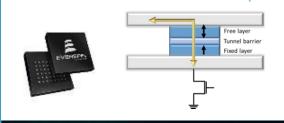
Product Portfolio Expands End Point Application Opportunity

Industrial/IoT Toggle MRAM



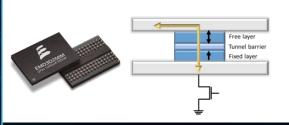
- SPI, QSPI, Parallel I/F
- 128 Kb to 32 Mb
- SRAM-like performance
- 20 years data retention
- -55C to 125C Operating Temp.
- Most robust MRAM

Industrial/IoT STT-MRAM



- SPI, QSPI, OSPI, xSPI
- 64 Mb to 256 Mb
- SRAM-like performance
- 10 years data retention
- -40C to 85C Operating Temp.
- Most affordable MRAM

Data Center STT-MRAM



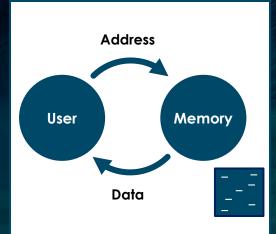
- ST-DDR3, ST-DDR4 I/F
- 256 Mb to 1 Gb
- DRAM-like performance
- 3 months to 10 years DR
- 0C to 85C Operating Temp.
- Highest density MRAM

Our new product development expands the opportunity for STT to existing and new MRAM customers



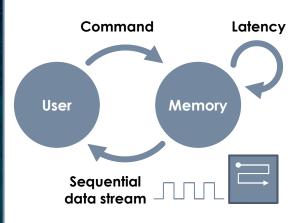
Memory Interfaces Enabling MRAM Applications

Parallel



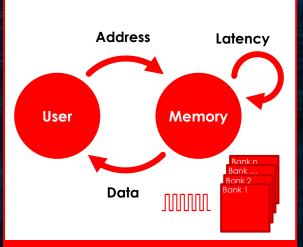
- o Simple
- High pin count for bandwidth

Serial (SPI)



- o Simple
- Low pin count/small package
- Flexible (used for RAM, NOR and NAND)

Double Data Rate (DDR)



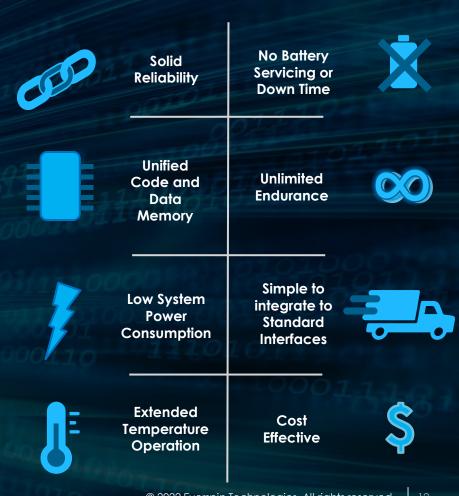
- Complex
- Optimized for DRAM and high bandwidth



MRAM in Industrial & IoT Universal Non-Volatile Memory

Bringing robust and simple nonvolatility to applications that need to store mission-critical data in CPU attached memory configurations





MRAM in the Data Center Lowest Latency Persistent Memory

Addressing the need for assured data integrity in high performance data buffering applications with unmatched endurance and reliability



Enterprise Storage



Enterprise Server RAID



Persistent Memory



Fabric Accelerator



Solid Reliability

No Stored Energy Liability





Larger Buffer Improves Latency QOS

No Capacitor Backed RAM





Optimized
Interleave For
Sequential
Performance

Simplified
Architecture
Eliminates Power
Fail Hardenina





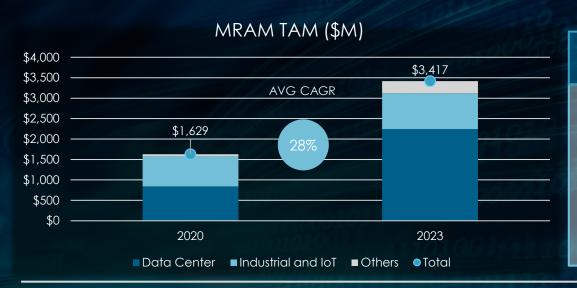
More Physical Space For Storage Capacity

Enable Higher Number of Streams





Market Potential In Data Center Core And Industrial/IoT End Points



KEY SUCCESS FACTORS

- Focus on high value segments that need higher performance and reliability
- STT-MRAM penetration in Data Center Core Applications
- Expand opportunities for MRAM with Industrial/IoT STT-MRAM
- Enhanced feature set for unified memory

CURRENT FOCUS SEGMENTS



Enterprise Storage



Enterprise Server RAID



Industrial Automation



Medical



Network & Infrastructure



Casino Gaming



Other Industrial

GROWTH OPPORTUNITIES



Persistent Memory



FPGA Applications



Mil/Aero



Transportation



Diversified Top-Tier Customer Base in Significant Markets

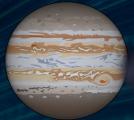


Serving some of the most demanding customers in segments with long-term stability



Everspin MRAM in Mission Critical Applications

And Beyond...



On its way to Jupiter in NASA's Lucy Mission

On Mars



In a NASA Mars rover camera, Perseverance.

On Earth



In master power train system of Lucid Air EV

- MRAM is better suited for harsh environments compared with charge-based memories (DRAM, SRAM, and Flash).
 - High-radiation environments for space, defense, and telecommunications applications
 - High temperatures in the automotive area



Industrial/IoT STT-MRAM: Customer Use Examples

Industrial PLC Portfolio (Design into entire portfolio)

High density & Fast SCRAM (up-to 512Mb)







Key early customer engagements with broad Toggle customer base



EMxxLX – The Best of All Worlds in One Memory

Performance

- Standard xSPI interface with support up to 400MBps
- Over 100 times faster write performance than NOR
- No Erase required

Endurance & Retention

- Unlimited Endurance
- Reduces the need for flash over-provisioning
- 10 years data retention at 85C

EVERSPIN

EM064LX STT MRAM: Now under customer evaluation!

Unified Memory

- Combine multiple memories into one.
- Provides NOR flash functions as well as nvRAM
- No need for battery back up RAM.

Low Power

- Deep power down modes
- Fast boot up from power down. 1.8 Voltage support
- Low energy, fast writes

Erase/Program
time shrinks from
Minutes with
NOR to seconds
with MRAM



MRAM: IoT and Far Edge Application Benefits

Data protected from power loss

Faster standard interfaces to support increasing processing needs

No Erase required simplifying software

High Endurance reducing the complexity of NOR provisioning Faster writes reduces energy and improves faster OTA updates

Density continues to scale for unified memory needs

5G bandwidth brings new business models to connected, embedded systems

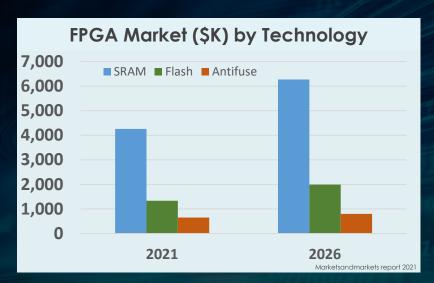
- Software defined services and features
- Over-the-Air (OTA) updating of software

- NOR Flash, at \$2.7B*, is the predominant memory for application code storage
 - Density not scaling well beyond 256Mb
 - Slow program time
 - Wears out quickly
- Opening for MRAM to satisfy the future needs
- Everspin now developing higher density, unified memory with enhanced feature set.
 - First 22nm product in design



^{* 2022} analysis by The Insight Partners

FPGA Market Opens New Uses for MRAM



- Flash based growing 8.4% CAGR driven by Instant-on, low power apps.
 - But Flash not scaling well below 40nm
- FPGA market has associated memory market of 100Mu+ for configuration and data memory.

- MRAM as external configuration memory, replacing NOR Flash where configuration time is critical
 - Everspin EM064LX addresses >70% of the market, low to mid-range of FPGA
 - Next product covers high end as well
- MRAM as a block memory chiplet to provide instant on, fast reconfiguration, non-volatile data memory and low power
 - Everspin working with FPGA vendors on chiplet definition
- New concepts
 - MRAM bit as a configuration element
 - Initial market in mil/aero



Everspin IP Delivers Value Through Licensing

Magnetic Sensors

Mil-Aero Toggle MRAM

Embedded STT-MRAM

Head Sensor





Honeywell









Everspin has successfully licensed MRAM, 3D Magnetic Sensor and TMR Head Sensor (HDD) IP

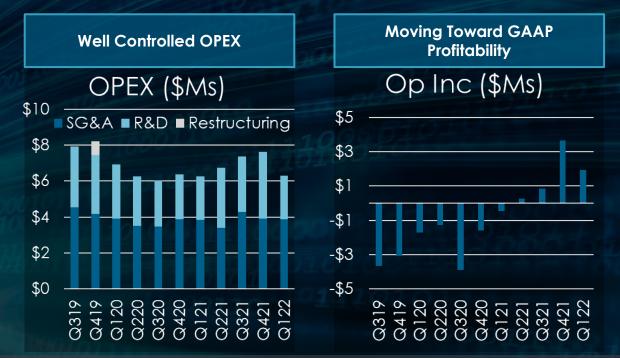




Key Financial Indicators

As of Q1'2022





Q3'20 gross margin reflected a \$1.7M non-cash charge related to excess and obsolete inventory reserve, \$0.4M accelerated depreciation, and a \$0.1M prior period cost
adjustment

Everspin is focused on building a sustainable business model



Income Statement

| (\$M) | 1Q20 | 2Q20 | 3Q20 | 4Q20 | 1Q21 | 2Q21 | 3Q21 | 4Q21 | 1Q22 |
|--------------|---------|---------|---------|---------|--------|--------|--------|--------|--------|
| Revenue | \$10.1 | \$11.8 | \$10.1 | \$10.0 | \$10.3 | \$11.8 | \$14.8 | \$18.2 | \$14.3 |
| Gross Profit | \$5.4 | \$5.2 | \$2.3 | \$5.2 | \$6.0 | \$7.2 | \$8.4 | \$11.4 | \$8.3 |
| R&D | \$3.0 | \$2.8 | \$2.6 | \$2.5 | \$2.4 | \$3.4 | \$3.1 | \$3.7 | \$2.4 |
| SG&A | \$3.9 | \$3.5 | \$3.5 | \$3.9 | \$3.8 | \$3.4 | \$4.3 | \$3.9 | \$3.9 |
| Net Income | (\$1.7) | (\$1.3) | (\$3.9) | (\$1.6) | (0.5) | \$0.3 | \$0.9 | \$3.7 | \$1.9 |

Q3'20 results reflect a \$1.7M non-cash charge related to excess and obsolete inventory reserve, \$0.4M accelerated depreciation, and a \$0.1M prior period cost adjustment



Balance Sheet

| (\$M) | 1Q20 | 2Q20 | 3Q20 | 4Q20 | 1Q21 | 2Q21 | 3Q21 | 4Q21 | 1Q22 |
|--------------------|--------|--------|--------|--------|--------|--------|--------|--------|--------|
| Cash & Equivalents | \$14.0 | \$12.9 | \$13.9 | \$14.6 | \$15.5 | \$14.2 | \$14.6 | \$21.4 | \$19.9 |
| Assets | \$34.7 | \$35.1 | \$33.2 | \$32.5 | \$35.1 | \$34.6 | \$34.9 | \$39.4 | \$42.7 |
| Debt | \$7.9 | \$7.9 | \$7.9 | \$7.9 | \$7.5 | \$7.0 | \$5.5 | \$4.9 | \$4.3 |
| Liabilities | \$14.7 | \$14.7 | \$15.3 | \$15.1 | \$16.9 | \$15.3 | \$13.6 | \$12.2 | \$12.6 |
| Equity | \$20.0 | \$20.4 | \$18.0 | \$17.4 | \$18.2 | \$19.3 | \$21.3 | \$27.2 | \$30.1 |

Raised an aggregate of \$6.9M in net proceeds from ATM facility in 3Q19 through 1Q20 periods. ATM sales were suspended in March 2020, and the ATM program terminated in November 2020

Refinanced debt in August 2019 and further amended credit agreement in July 2020, which delays principal payments until January 2021, significantly reducing debt service costs



Key Investor Takeaways

Unique success producing high-value discrete MRAM products over 5 generations of technology

Addressing needs of Tier-1 customers in stable and growing markets from Data Centers to Industrial & IoT Edge Devices

Strong IP portfolio of over 650 patents and applications generating licensing and royalty revenue

Solid track record of revenue growth, strong margins and cost control building increasing financial stability

Solid Toggle MRAM customer base with growing design wins and growing market opportunity for STT-MRAM with large potential

Leadership Team with experience commercializing technology in our target markets





Appendix

Fab Partnership Expansion to Meet The Growing Demand



Strong Partnership with GF for STT-MRAM

- 40nm 256Mb discrete chip mass production
- 28nm 1Gb discrete chip mass production
- 22nm FDX embedded for GF SOC customer pilot
- 12nm Joint Development Agreement announced

Stability for MRAM

Long-term Chandler manufacturing operation continues (production since 2006)



- Multi-year manufacturing contract in place
- Toggle and STT– MRAM production capability

Established manufacturing partnerships for long term growth



5 Global Operation Sites & 8 Regional Offices



